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number. Substitute for form 1449A/PTO Complete If Known Application Number Filing Date 10/664,072 INFORMATION DISCLOSURE September 16, 2003 First Named Inventor Mahendra Kumar Sunkara STATEMENT BY APPLICANT Art Unit 1722 (use as many sheets as necessary) Examiner Name

Sheet 1 of Attorney Docket Number | AD138/2001

Examiner Initials*	Cite No.1	Number-Kind Code ² V US 5,725,674	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear Throughout	
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